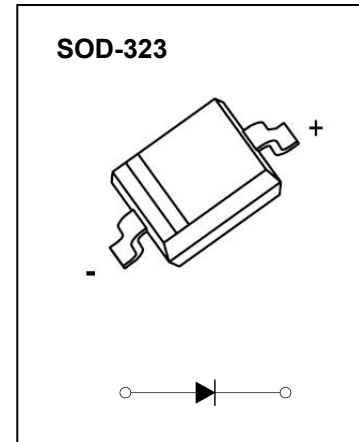


# SOD-323 Plastic-Encapsulate Diodes

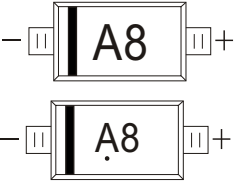
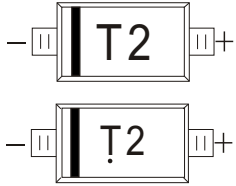
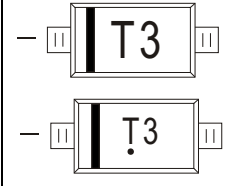
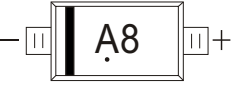


## BAV19WS~BAV21WS SWITCHING DIODE

### FEATURES

- Low Reverse Current
- Surface Mount Package Ideally Suited for Automatic Insertion
- Fast Switching Speed
- For General Purpose Switching Applications



### MARKING:

BAV19WS A8	BAV20WS T2	BAV21WS T3
		
		

The marking bar indicates the cathode  
Solid dot = Green molding compound device,  
if none, the normal device.

### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted )

Symbol	Parameter	Value			Unit
		BAV19WS	BAV20WS	BAV21WS	
$V_{RM}$	Non-Repetitive Peak Reverse Voltage	120	200	250	V
$V_{RRM}$	Peak Repetitive Reverse Voltage	100	150	200	V
$V_{RWM}$	Working Peak Reverse Voltage				
$V_{R(RMS)}$	RMS Reverse Voltage	71	106	141	V
$I_O$	Average Rectified Output Current	200			mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2.0			A
$P_D$	Power Dissipation	250			mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500			$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150			$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150			$^{\circ}\text{C}$

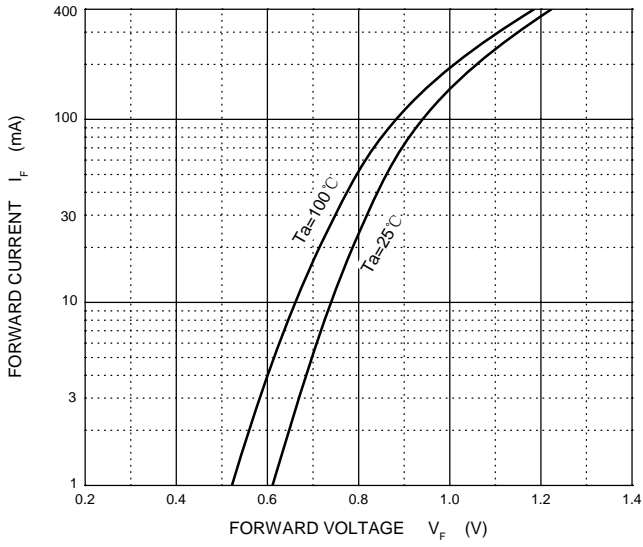
### ELECTRICAL CHARACTERISTICS( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R=100\text{V}$	BAV19WS		0.1	uA
		$V_R=150\text{V}$	BAV20WS		0.1	
		$V_R=200\text{V}$	BAV21WS		0.1	
Forward voltage	$V_F$	$I_F=100\text{mA}$			1	V
		$I_F=200\text{mA}$			1.25	
Total capacitance	$C_{tot}$	$V_R=0\text{V}, f=1\text{MHz}$			5	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=30\text{mA}, I_{rr}=0.1 \cdot I_R, R_L=100\Omega$			50	ns

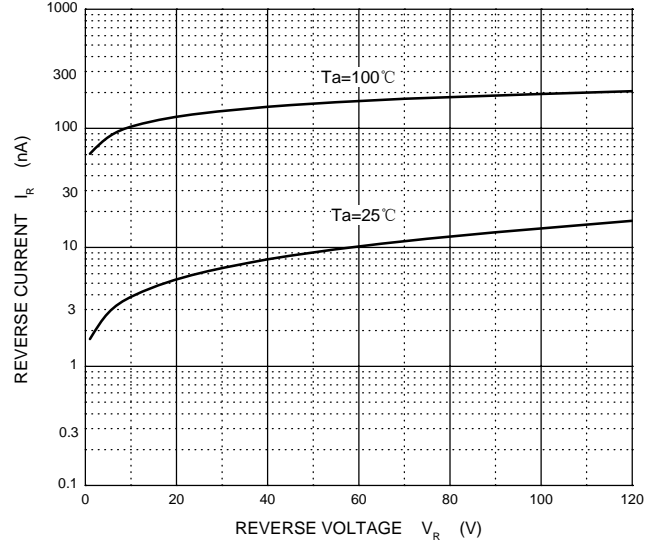


### BAV19WS Typical Characteristics

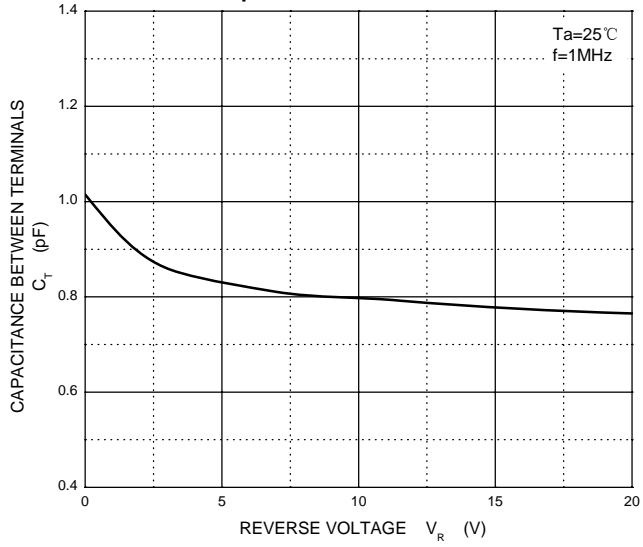
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

